

Amendments to the Specification:

Please replace the paragraph that begins at page 3, line 5, with the following amended paragraph:

The invention relates to micromachining methods using CMP. Thus, in a first aspect the invention provides a method for forming a substrate into a defined structure, said method comprising selectively removing at least a portion of the substrate by chemical mechanical polishing to provide the defined structure, wherein the defined structure is at least partially non-planar. Preferably, the removal of substrate is by a combination of chemical etch and mechanical polishing.

Please replace the paragraph at page 3, line 20, with the following amended paragraph:

Fig. 5A illustrates polishing of a feature by a pad having asperities on its surface.

Please add the following new paragraph immediately after the paragraph at page 3, line 20:

Fig 5B illustrates areas of local curvature on a polishing pad provided by bumps under the pad.

Please replace the paragraph that begins at page 4, line 21, with the following amended paragraph:

In the invention, the characteristics of the polishing pad are varied such that the CMP polish, including the optional use of a chemical slurry, provides structures that are at least partially non-planar. The polishing pad characteristics that can be varied include the stiffness of the pad. Pad stiffness can be manipulated by several properties of the CMP apparatus, including downforce on the polishing pad; rotational velocity of the polishing pad; and acceleration velocity of the polishing pad. In addition, stiffness is also a function of the pad material. Other pad characteristics that are advantageously utilized in the invention to form partially non-planar structures include areas of local curvature on the pad, areas of local increased or decreased downforce on the pad, and the presence of asperities 40 (Fig. 5A) on the pad. In addition, the position of the polishing pad relative to the substrate being polished, can be exploited to provide structures that are partially non-planar. Areas of local curvature 60 on the pad 20 may be provided by bumps 65 under the pad (Fig. 5B).